

| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|--|--------------------------------|------------------|
| 26 | 0 | 6586082.pn. | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:01 |
| 31 | 1 | 6526082.pn. | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:11 |
| 36 | 0 | 6526082.pn. and polarization | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:15 |
| 41 | 96 | (semiconductor near2 laser) and (active with polariz\$5) and junction | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:19 |
| 46 | 37 | ((semiconductor near2 laser) and (active with polariz\$5) and junction) and (n near3 layer) and (p near3 layer) | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:17 |
| 51 | 0 | (semiconductor near2 laser) and ((active near2 (layer region area)) same (polarization near3 field)) and (("p-n") "n-p" near2 junction) | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:22 |
| 56 | 5 | (semiconductor near2 laser) and ((active near2 (layer region area)) same (polarization near3 field)) | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:25 |
| 61 | 339 | (semiconductor near2 laser) and ((active near2 (layer region area)) same polarization) | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:26 |
| 66 | 30 | ((semiconductor near2 laser) and ((active near2 (layer region area)) same polarization)) and ((p near2 n) near2 junction) | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:45 |
| 71 | 0 | ((semiconductor near2 laser) and ((active near2 (layer region area)) same polarization)) and ((p near2 n) near2 junction)) and tunnel with diode | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:45 |
| 76 | 40 | reverse with bias\$3 with tunnel with diode | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:46 |
| 81 | 1 | (reverse with bias\$3 with tunnel with diode) and polarization | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:46 |
| 86 | 13154 | reverse with bias\$3 with diode | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:47 |
| 91 | 234 | (reverse with bias\$3 with diode) and semiconductor and polarization | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:47 |
| 96 | 0 | ((reverse with bias\$3 with diode) and semiconductor and polarization) and (((semiconductor near2 laser) and ((active near2 (layer region area)) same polarization)) and ((p near2 n) near2 junction)) | USPAT; EPO; JPO; IBM_TDB | 2003/03/20 22:47 |
| 101 | 7 | (US-5953362-\$ or US-5828684-\$ or US-5764676-\$ or US-5757828-\$ or US-5383211-\$ or US-5331654-\$ or US-5070510-\$).did. | USPAT | 2003/03/20 22:47 |